

ABSTRACT

An integrated circuit and manufacturing method therefor is provided having a semiconductor substrate with a semiconductor device. A dielectric layer formed over the semiconductor substrate has an opening provided therein. The dielectric layer is of non-
5 barrier dielectric material capable of being changed into a barrier dielectric material. The dielectric layer around the opening is changed into the barrier dielectric material and the conductor core material is deposited to fill the opening. The conductor core is processed to form a channel for the integrated circuit.